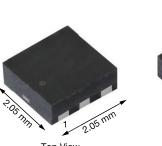
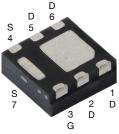
SQA470CEJW

www.vishay.com

Vishay Siliconix

Automotive N-Channel 30 V (D-S) 175 °C MOSFET





Bottom View

Top View Marking Code: QXXXXX

 PRODUCT SUMMARY

 V_{DS} (V)
 30

 $R_{DS(on)}$ (Ω) at V_{GS} = 4.5 V
 0.065

 $R_{DS(on)}$ (Ω) at V_{GS} = 2.5 V
 0.095

 I_D (A)
 2.25

 Configuration
 Single

PowerPAK[®] SC-70W-6L Single

FEATURES

- TrenchFET[®] power MOSFET
- AEC-Q101 qualified
- Wettable flank terminals
- 100 % R_{α} and UIS tested
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>



FREE

G

N-Channel MOSFET

ORDERING INFORMATION			
Package	PowerPAK SC-70W-6L		
Lead (Pb)-free and halogen-free	SQA470CEJW (for detailed order number please see <u>www.vishav.com/doc?79776</u>)		

ABSOLUTE MAXIMUM RATINGS (T _C = 25 °C, unless otherwise noted)						
PARAMETER	SYMBOL	LIMIT	UNIT			
Drain-source voltage		V _{DS}	30	V		
Gate-source voltage		V _{GS}	± 12	v		
	T _C = 25 °C	- I _D	2.25			
Continuous drain current ^a	T _C = 125 °C		2.25			
Continuous source current (diode conduction) ^a		IS	2.25	А		
Pulsed drain current ^a		I _{DM}	9			
Single pulse avalanche current	L = 0.1 mH	I _{AS}	9			
Single pulse avalanche energy	L = 0.1 MH	E _{AS}	4	mJ		
laximum power dissipation	T _C = 25 °C	PD	13.6	W		
	T _C = 125 °C		4.5	vv		
Operating junction and storage temperature	range	T _J , T _{stg}	-55 to +175	°C		
Soldering recommendations (peak temperat	ture) ^{d, e}		260	C		

THERMAL RESISTANCE RATINGS					
PARAMETER		SYMBOL	LIMIT	UNIT	
Junction-to-ambient	PCB mount ^c	R _{thJA}	90	°C/W	
Junction-to-case (drain)		R _{thJC}	11	0/10	

Notes

a. Package limited

b. Pulse test; pulse width \leq 300 µs, duty cycle \leq 2 %

c. When mounted on 1" square PCB (FR4 material)

e. Rework conditions: manual soldering with a soldering iron is not recommended for leadless components

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d. See solder profile (<u>www.vishay.com/doc?73257</u>). The PowerPAK SC-70W-6L is a leadless package and features wettable flank terminals. The end of the lead terminal is plated with tin.

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PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT	
Static				•	•			
Drain-source breakdown voltage	V _{DS}	$V_{GS} = 0 V, I_D = 250 \mu A$		30	-	-	v	
Gate-source threshold voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_D = 250 \ \mu A$		0.6	1.0	1.3		
Gate-source leakage	I _{GSS}	V _{DS} =	$V_{DS} = 0 V, V_{GS} = \pm 12 V$			± 100	nA	
ro gate voltage drain current	I _{DSS}	$V_{GS} = 0 V$	V _{DS} = 30 V	-	-	1		
		$V_{GS} = 0 V$	V _{DS} = 30 V, T _J = 125 °C	-	-	50	μA	
		$V_{GS} = 0 V$	V _{DS} = 30 V, T _J = 175 °C	-	-	250		
On-state drain current ^a	I _{D(on)}	V _{GS} = 4.5 V	$V_{DS} \ge 5 V$	10	-	-	А	
	R _{DS(on)}	V _{GS} = 4.5 V	I _D = 3 A	-	0.038	0.065	Ω	
		$V_{GS} = 4.5 V$	I _D = 3 A, T _J = 125 °C	-	-	0.077		
Prain-source on-state resistance ^a		V _{GS} = 4.5 V	I _D = 3 A, T _J = 175 °C	-	-	0.090		
		V _{GS} = 2.5 V	I _D = 3 A	-	0.048	0.095		
Forward transconductance b	g fs	V _{DS}	= 15 V, I _D = 2 A	-	16	-	S	
Dynamic ^b		1 -		I	•			
Input capacitance	C _{iss}			-	312	440	pF	
Output capacitance	Coss	$V_{GS} = 0 V$	V _{DS} = 20 V, f = 1 MHz	-	56	80		
Reverse transfer capacitance	C _{rss}			-	29	41		
Total gate charge ^c	Qq	$V_{GS} = 4.5 \text{ V}$ $V_{DS} = 15 \text{ V}, I_D = 4.2 \text{ A}$		-	4.6	6		
Gate-source charge ^c	Qqs		-	0.65	-	nC		
Gate-drain charge ^c	Q _{qd}		-	0.9	-			
Gate resistance	R _q	f = 1 MHz		1.75	3.46	5.20	Ω	
Turn-on delay time ^c	t _{d(on)}	V_{DD} = 10 V, R _L = 10 Ω I _D \cong 1 A, V _{GEN} = 4.5 V, R _g = 1 Ω		-	7.3	11	- ns	
Rise time ^c	t _r			-	18	26		
Turn-off delay time ^c	t _{d(off)}			-	21	32		
Fall time ^c	t _f			-	9.5	14		
Source-Drain Diode Ratings and Charact	eristics ^b	·		•				
Pulsed current ^a	I _{SM}			-	-	9	А	
Forward voltage	V _{SD}	I _F = 4.5 A, V _{GS} = 0 V		-	0.75	1.2	V	
Body diode reverse recovery time	t _{rr}	I _F = 1.5 A, di/dt = 100 A/μs		-	12	24	ns	
Body diode reverse recovery charge	Q _{rr}			-	4	9	nC	
Reverse recovery fall time	ta			-	7	-	ns	
Reverse recovery rise time	t _b			-	5	-		
Body diode peak reverse recovery current	I _{RM(REC)}			-	-0.8	-	Α	

Notes

a. Pulse test; pulse width \leq 300 µs, duty cycle \leq 2 %

b. Guaranteed by design, not subject to production testing

c. Independent of operating temperature

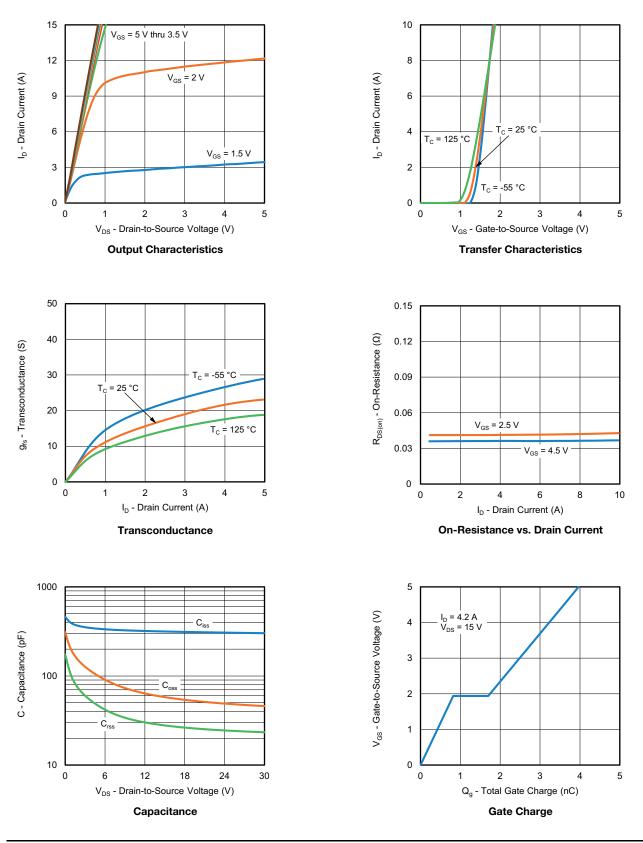
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

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TYPICAL CHARACTERISTICS ($T_A = 25 \text{ °C}$, unless otherwise noted)



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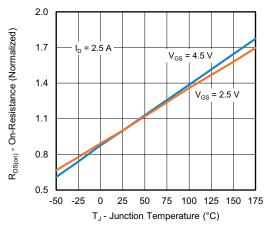
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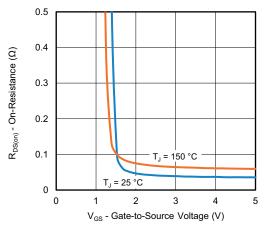


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TYPICAL CHARACTERISTICS ($T_A = 25 \text{ °C}$, unless otherwise noted)



On-Resistance vs. Junction Temperature



T_J = 150 °C

0.4

0.6

V_{SD} - Source-to-Drain Voltage (V)

Source Drain Diode Forward Voltage

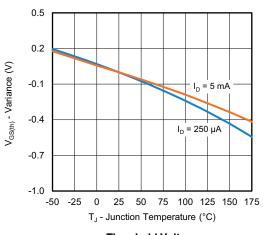
On-Resistance vs. Gate-to-Source Voltage

T_I = 25 °C

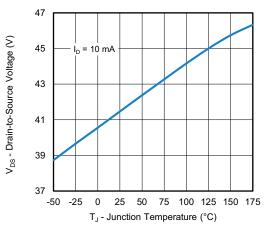
0.8

1.0

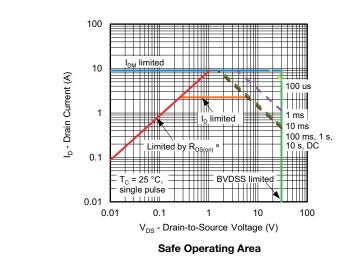
1.2







Drain Source Breakdown vs. Junction Temperature



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0.2

100

10

1

0.1

0.01

0

I_s - Source Current (A)

4

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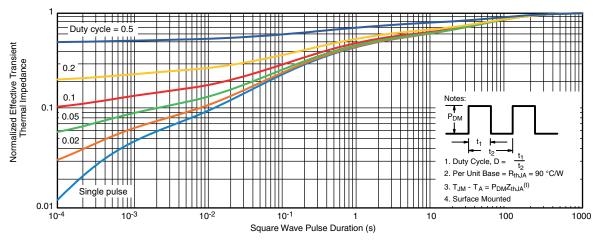
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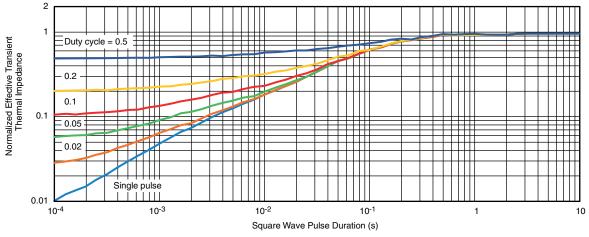


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THERMAL RATINGS (T_A = 25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Case

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